

# CD4071B, CD4072B, CD4075B Types

### **CMOS OR Gates**

#### High-Voltage Types (20-Volt Rating)

CD4071B	Quad	2-Input	OR	Gate
CD4072B	Dual	4-Input	OR	Gate
CD4075B	Triple	3-Input	OR	Gate

■ CD4071B, CD4072B, and CD4075B OR gates provide the system designer with direct implementation of the positive-logic OR function and supplement the existing family of CMOS gates.

The CD4071B, CD4072B, and CD4075B types are supplied in 14-lead hermetic dual-in-line ceramic packages (F3A suffix), 14-lead dual-in-line plastic packages (E suffix), 14-lead small-outline packages (M, MT, M96, and NSR suffixes), and 14-lead thin shrink small-outline packages (PW and PWR suffixes).

#### Features:

- Medium-Speed Operation-tpLH, tpHL = 60 ns (typ.) at VDD = 10 V
- = 100% tested for quiescent current at 20 V
- Maximum input current of 1 μA at 18 V over full package-temperature range; 100 nA at 18 V and 25<sup>o</sup>C
- Standardized, symmetrical output characteristics
- Noise margin (over full package temperature

range) 1 V at VDD = 5 V

- 2 V at VDD = 10 V
- 2.5 V at V<sub>DD</sub> = 15 V = 5-V, 10-V, and 15-V parametric ratings
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

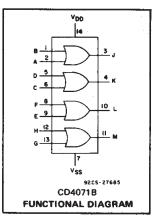
#### **RECOMMENDED OPERATING CONDITIONS**

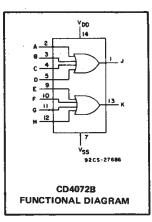
For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

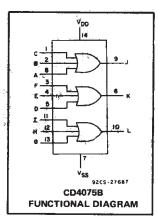
CHARACTERISTIC	LIN	UNITS	
	MIN.	MAX.	
Supply-Voltage Range (For T <sub>A</sub> = Full Package-Temperature Range)	3	18	v

#### STATIC ELECTRICAL CHARACTERISTICS

CHARACTER-	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)						UNITS		
ISTIC	vo	VIN	VDD						+25	r		
	(V)	(V)	(V)	-55	40	+85	+125	Min.	Тур.	Max.		
Quiescent Device		0,5	5	0.25	0.25	7.5	7.5	-	0.01	0.25		
	_	0,10	10	0.5	0,5	15	15	-	0.01	0,5	μΑ	
IDD Max.	-	0,15	15	1	1	30	30	-	0.01	1		
	-	0,20	20	5	5	150	150	-	0.02	5		
Output Low	0.4	0,5	5	0.64	0.61	0.42	0,36	0.51	1	-		
(Sink) Current	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	-		
IOL Min.	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	-	]	
Output High	4,6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	-	mA	
(Source)	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	-		
	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	-		
- OH IIIII	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	-		
Output Voltage:	_	0,5	5	0.05			-	0	0.05	v		
	_	0,10	10	0.05				0	0.05			
	-	0,15	15	0.05			-	0	0.05			
Current, IDD Max. Output Low (Sink) Current IOL Min. Output High (Source) Current, IOH Min. Output Voltage: Low-Level, VOL Max. Output Voltage: High-Level, VOH Min. Input Low Voltage, VIL Max. Input High Voltage, VIH Min.		0,5	5		4	.95		4.95	5	-	Ň	
	-	0,10	10		9	.95		9.95	10	-		
VOH MIN.	-	0,15	15		14	.95		14.95	15	-		
	0.5, 4.5		. 5		1	.5		-	- 1	1.5		
(Source) Current, IOH Min. Output Voltage: Low-Level, VOL Max. Output Voltage: High-Level, VOH Min. Input Low Voltage, VIL Max. Input High Voltage, VIH Min.	1, 9	_	10			3		-	—	3		
	1.5,13.5	÷	15	4			-	—	4	v		
	4.5	-	5		3	3.5		3.5		-	v	
	9		10			7		7	_			
VIH Min.	13.5		15	11			11		—			
Input Current IN Max.		0,18	18	±0.1	±0.1	±1	±1	-	±10 <sup>-5</sup>	±0.1	μА	





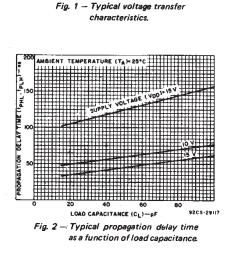


### CD4071B, CD4072B, CD4075B Types

MAXIMUM RATINGS, Absolute-Maximum Values:
DC SUPPLY-VOLTAGE RANGE, (VDD)
Voltages referenced to V <sub>SS</sub> Terminal)
INPUT VOLTAGE RANGE, ALL INPUTS
DC INPUT CURRENT, ANY ONE INPUT
POWER DISSIPATION PER PACKAGE (PD):
For T <sub>A</sub> = -55°C to +100°C
For T <sub>A</sub> = +100°C to +125°CDerate Linearity at 12mW/°C to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR
FOR TA = FULL PACKAGE-TEMPERATURE RANGE (All Package Types)
OPERATING-TEMPERATURE RANGE (TA)
STORAGE TEMPERATURE RANGE (Tstg)
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 ± 1/32 inch (1.59 ± 0.79 mm) from case for 10s max

DYNAMIC ELECTRICAL CHARACTERISTICS at  $T_A = 25^{\circ}C$ , input  $t_r$ ,  $t_f = 20$  ns, and CL = 50 pF, RL = 200 k $\Omega$ 

CHARACTERISTIC	TEST CONDITIONS		ALL TYPES LIMITS		
	· · · · · · · · · · · · · · · · · · ·	V <sub>DD</sub> VOLTS	TYP.	MAX.	
Propagation Delay Time,	· · · · · · · · · · · · · · · · · · ·	5	125	250	1
tPHL, tPLH		10	60	120	ns
		15	45	90	
Transition Time,		5	100	200	
tTHL, TTLH		10	50	100	ns
THUMLH		15	40	80	· ·
Input Capacitance, CIN	Any Input		5	7.5	pF



BIENT TEMPERATURE (TA)=25°C 

SUP

VOLTAGE ( VO)

OUTPUT

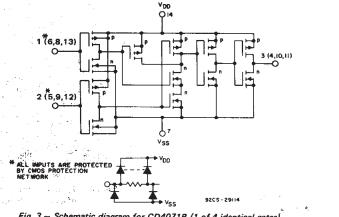
VOI TAGE

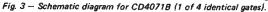
INPUT VOLTAGE (VIN) - V

9205-29110

3

COMMERCIAL CMOS HIGH VOLTAGE ICS





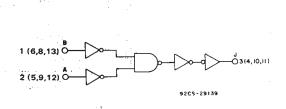


Fig. 5 -/ Logic diagram for CD4071B (1 of 4 identical gates).

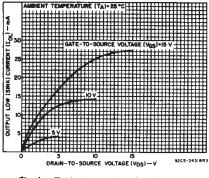
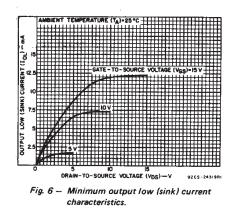
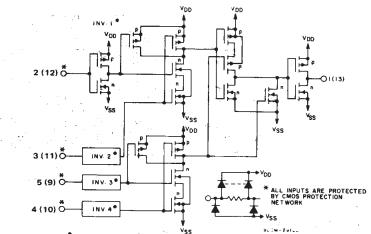


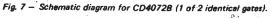
Fig. 4 - Typical output low (sink) current characteristics.

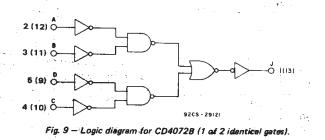


### CD4071B, CD4072B, CD4075B Types



INVERTERS 2,3 AND 4 ARE IDENTICAL TO INVERTER 1





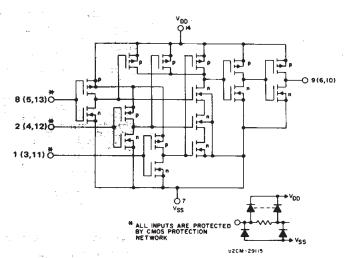
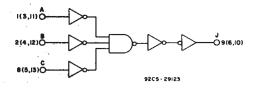
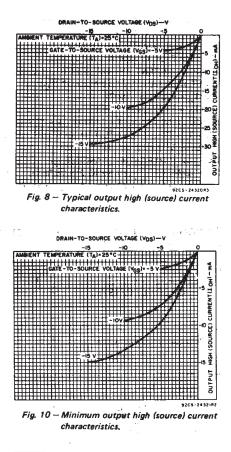


Fig. 11 - Schematic diagram for CD4075B (1 of 3 identical gates).







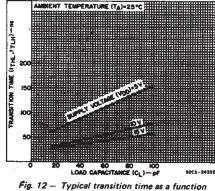


Fig. 12 — Typical transition time as a function of load capacitance.

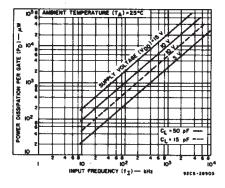
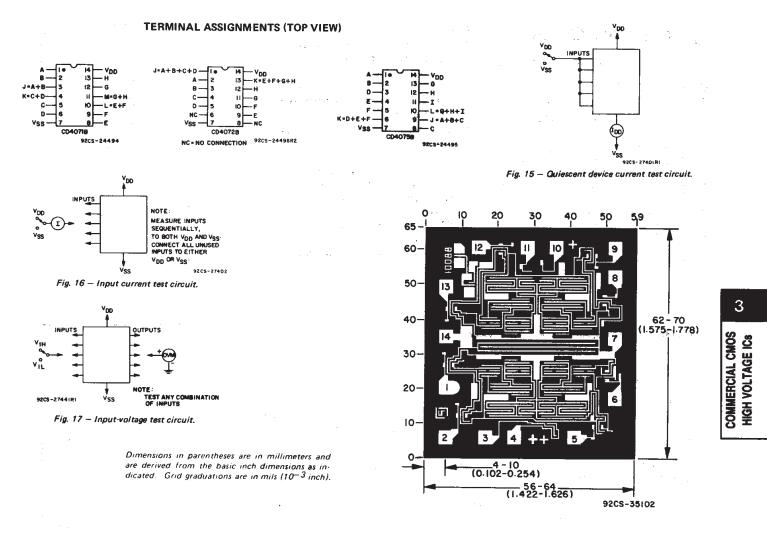
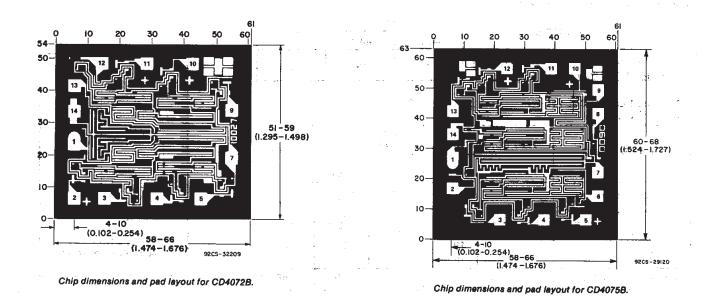


Fig. 14 – Typical dyanamic power dissipation as a function of frequency.

1.1



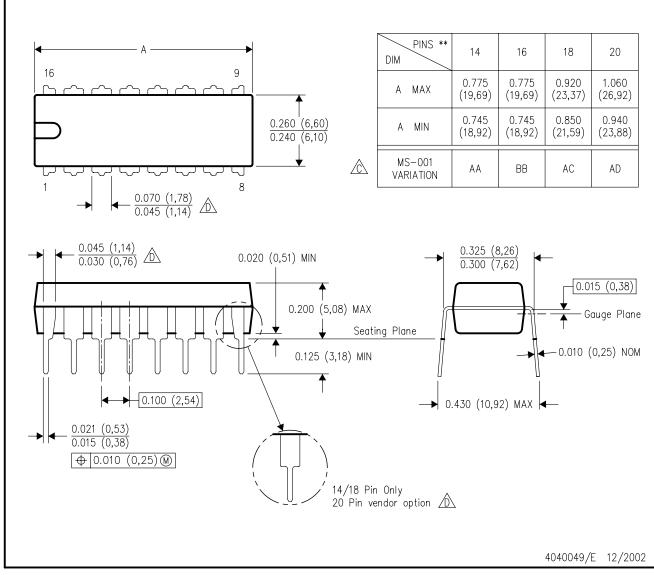
Chip dimensions and pad layout for CD4071B.



## N (R-PDIP-T\*\*)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN

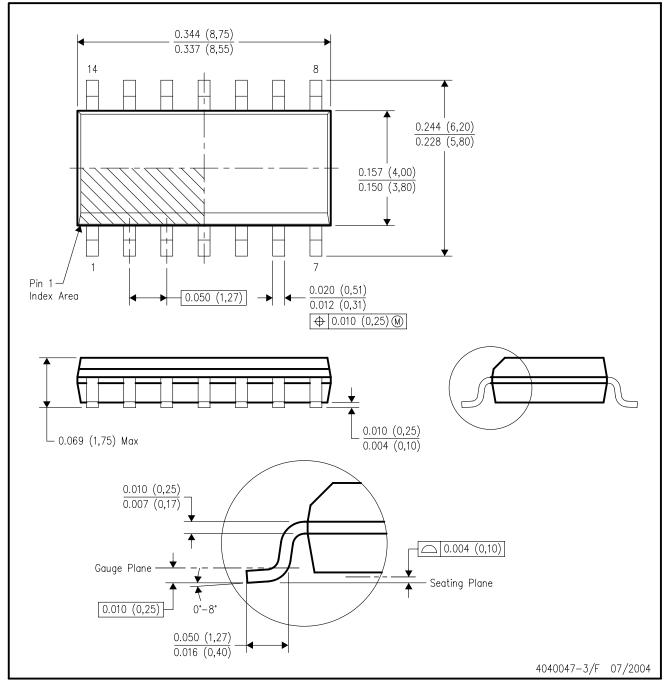


NOTES:

- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- $\triangle$  The 20 pin end lead shoulder width is a vendor option, either half or full width.

D (R-PDSO-G14)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-012 variation AB.